

ABSTRACT OF THE DISLOSURE

A method of enabling the removal of fluorine containing residue from a semiconductor substrate comprising applying a gas and/or vapor to which the residue is reactive to the residue while the temperature of the
5 substrate is at an elevated level with respect to ambient temperature and the residue is exposed to ultraviolet radiation, for a time period which is sufficient to effect at least one of volatilizing the residue or rendering the residue hydrophilic enough to be removable with deionized water.